

MARKED-UP COPY OF AMENDMENTS TO THE CLAIMS

35. (Twice Amended) A method of fabricating a semiconductor structure, the method comprising the steps of:

providing a semiconductor substrate; ~~and~~

providing on said substrate a graded region incorporating ~~compressive~~ a first type of strain; and

processing the graded region so as to introduce a second type of strain, the previously incorporated first type of strain reducing the process-induced to offset tensile second type of strain arising during processing.

39. (Twice Amended) The method of claim ~~35~~45, wherein the graded region comprises Si and Ge graded to an increasing concentration of Ge, and the step of incorporating compressive strain comprises decreasing a temperature at which the graded region is grown as the Ge concentration increases in ~~said~~ the graded region.

40. (Amended) The method of claim 39, wherein ~~said~~ the step of incorporating ~~compressive~~ compressive strain comprises growing alloys of $\text{Ge}_x\text{Si}_{1-x}$ from $x = 0$ to about $x \approx 35\%$ at 750°C , growing alloys from $x = 35$ to about $x \approx 75\%$ at between 650°C and 750°C , and growing alloys greater than 75% at 550°C .

41. (Amended) The method of claim ~~35~~44, wherein said step of planarizing comprises chemical-mechanical polishing.

~~42. The method of claim 35, wherein said region is partially relaxed.~~

~~43. The method of claim 35, wherein said region is fully relaxed.~~

44. (New) The method of claim 35, further comprising the step of planarizing at least one surface of the structure.

45. (New) The method of claim 35, wherein the first type of strain is compressive strain and the second type of strain is tensile strain.